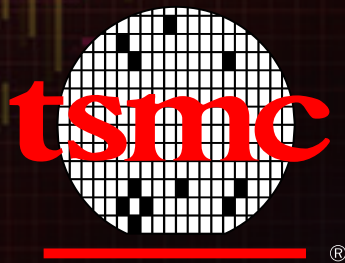


Enabling the Expanding Cloud: High-Bandwidth Memory and 2.5D Solutions

eSilicon Corp.



TSMC 2016
Open Innovation Platform®
Ecosystem Forum

ABSTRACT

The next generation of high-performance computing, graphics and networking applications have increasing needs for bandwidth. If we look at a traditional ASIC with external memory, the complete system is large with many DRAMs taking up board real estate affecting the performance and power consumption. The performance suffers from increased latency of the signals and more power results from driving these signals. In addition to this, there is a significant growth of the number of tracks on the substrate as well as an increase in the number of die leading to routing congestion.

DRAM technology has not been scaling to keep up with this need. The answer is moving to a stacked memory solution – high-bandwidth memory (HBM). This memory has been defined as a JEDEC standard, JESD235A, and began production in 2015. The use of HBM requires 2.5D packaging with silicon interposer and through-silicon vias.

2.5D technology offers a tremendous increase in capacity and performance. Increased capacity because of the stacked memory in a smaller area and increased performance because of the interposer and shorter signal routing. The interposer allows the integration of highly parallel connections to the memory stacks inside the package, therefore it is able to offer huge capacity and performance increases.

eSilicon started a program called “Modular Z-axis Integration” or MoZAIC in 2011. As an ASIC provider of large, complex networking and communication systems, we began analyzing new approaches that would provide more bandwidth for our customers. This includes the development of an HBM PHY in 28nm and FinFET technologies as well as the study of 2.5D packaging. eSilicon has completed seven test chips to date that verify the HBM PHY IP and to vet the supply chain in support of 2.5D integration — design, verification, test and reliability.


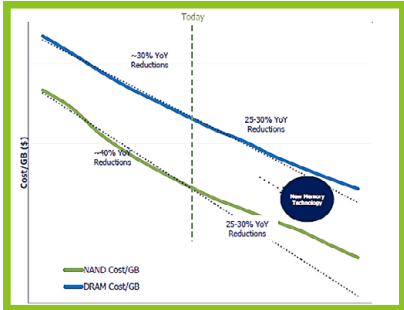
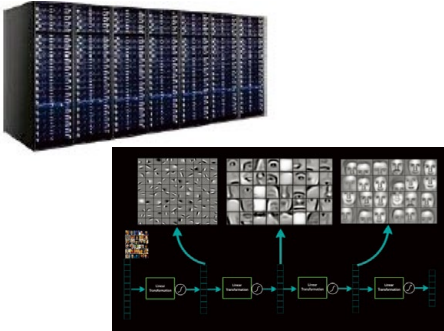
This presentation will highlight the silicon characteristics of eSilicon’s HBM PHY in TSMC’s CLN28HPC technology. The presentation will also highlight TSMC CoWoS technology as well as complex ASICs that use high-bandwidth memory.

Enabling the Expanding Cloud: High-Bandwidth Memory and 2.5D Solutions



Lisa Minwell
SR. DIRECTOR IP MARKETING

What's Driving High Bandwidth Memory?






Source: Mike Black, Micron, EDPS 2013

- DRAM technology in sub-20nm technologies faces severe challenges, such as difficulties in obtaining sufficient storage capacitance and sensing margin leading to stacked memory
- The need for increased bandwidth is driven by the growing IoT cloud, deep learning and neural networks

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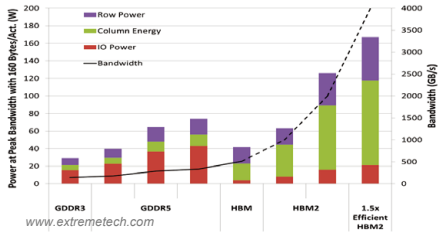
The Power Problem



- Limited bandwidth of DDRx devices now requires very high numbers of DRAM devices connected to the central ASIC
 - To buffer 1Tbps would require 40 DDR3 DRAMs all connected through separate buses
- ASICs are already at >1,500 pins and typically pin-limited. Very difficult to increase bandwidth to memory using current approach
- DDR4 does not solve the problem – 1Tbps requires 20 DDR4 DRAMs

Ratio (mW/Gbps/Pin)


Technology	Ratio (mW/Gbps/Pin)
DDR3x16	1
DDR4x16	0.63
GDDR5x32	0.55
HBM	0.32



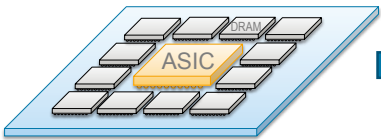
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2.5D Increases Bandwidth

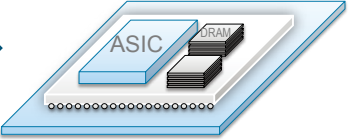


**ASIC plus multiple
DRAMs**



➔

**Single package - ASIC
plus memory stack(s)**



- Using an interposer allows the integration of highly parallel connections to memory stacks inside the package
- Much higher total bandwidth
- Significant reduction in power consumption
- Much smaller board footprint

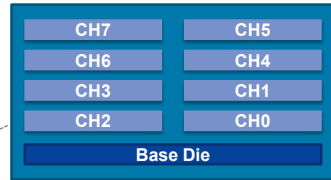
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2.5D and HBM DRAM Architecture

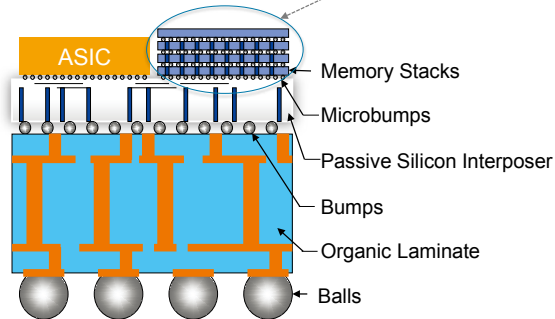


High-Bandwidth Memory Stack

- Base die – JTAG, BIST, PHY, through-silicon via (TSV) and DA interfaces
- Core die – (CH0 – CH7) DRAM circuitry and TSV interface

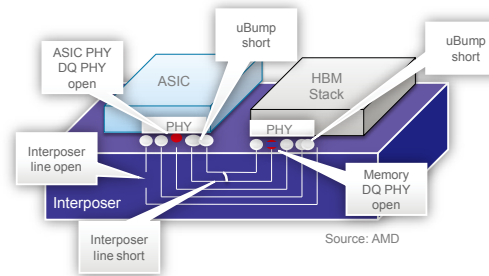


HBM Four-High Stack



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HBM Implementation Has Its Challenges



Challenges:

8192-bit-wide memory bus is, by conventional standards, absurdly wide, requiring thousands of contacts and traces

The key challenge is that the max junction temp acceptable for the HBM2 die is a lot **lower** than the ASIC while at the same time the thermal coupling to the high-power ASIC is **significant**.

Solutions:

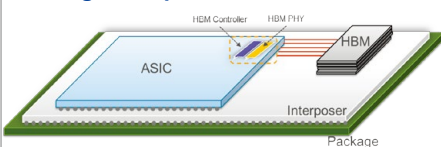
- Repair interconnection failure between SoC and HBM using MISR test to validate connections
- Redundant uBumps used for AWORD/DWORD repair
- Careful thermal and power analysis for the entire module in the design phase and additional thermal test vehicles to validate thermal and reliability assumptions

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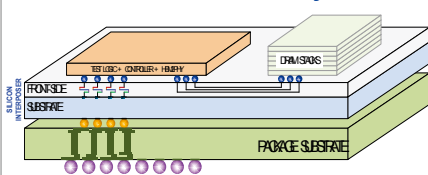
HBM Implementation Recipe



Design & Implementation



Characterization, Reliability & Test



HBM PHY & Controller

- Hardened for optimal speed and integration
- Supports multiple HBM vendors for expanded supply chain

Interposer Design

- Single and power integrity
- Thermal and warpage analysis

Characterization

- Fully tested to meet performance

Reliability & Testability

- Package test
- Assembly stacking
- HTS, pre-conditioning, TC and unbiased HAST

Wide Supply Chain

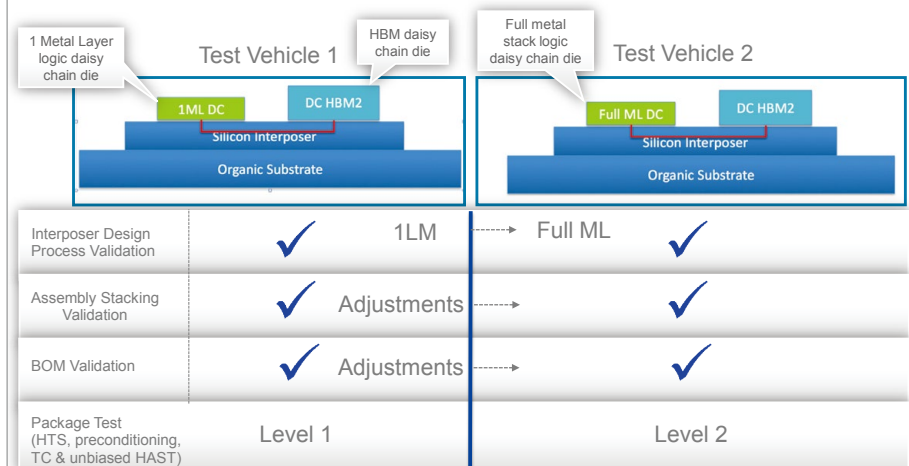
- Lowest cost
- Fastest time to market

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Proving the Supply Chain FinFET Logic Die and Silicon Interposer



Incremental test vehicles enable customers to meet tight schedule deadlines while implementing this new technology

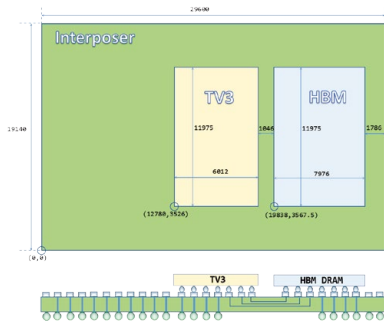


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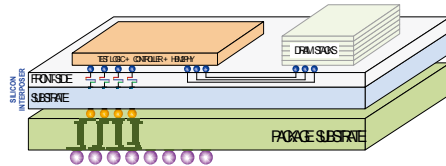
HBM PHY Test System Interposer – Test Vehicle 3



eSilicon leverages both ASIC and IP design



- Thermal test vehicle combined with the IP qualification vehicle (TV3)
- PHY development and test
- Interposer design
- Packaging
- Warpage analysis



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eSilicon's HBM IP Manufacturing Tests

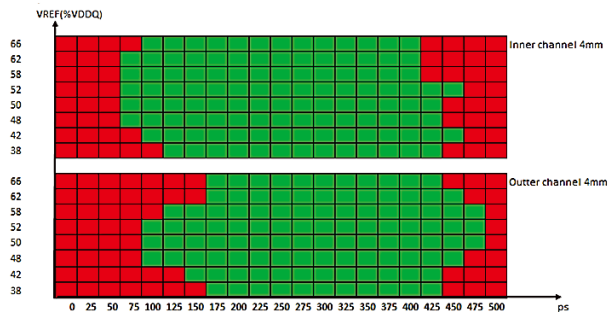
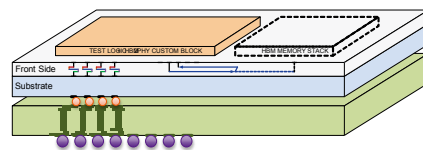


Test	ASIC Wafer	ASIC Die & Interposer & Package	Package; Includes HBM2	Notes
PLL Test	X	X	X	
DLL BIST	X	X	X	Validate every DLL delay line tap
HBM Internal Loopback	X	X	X	Through driver, to-pad
SerDes Internal Loopback	X	X	X	
SerDes External Loopback		X	X	
HBM Memory Soft Repair			X	Hard repair done in memory manufacturing test
PMBIST ASIC DRAM Test			X	Soft programmable
ASIC/HBM MISR AC Test			X	LFISR/MISR through IEEE-1500 interface
uBump Soft Repair			X	Based on MISR test results
HBM DC Boundary Scan			X	IEEE-1500 based – post MISR/repair
PVT Sensors	X	X	X	Through-tap controller. Burn at wafer if trimming needed
ChipID/eFuse	X	X	X	Through-tap controller. Burn at wafer
Functional Vectors	X	X	X	For scan AU fault detection

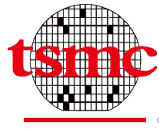
eSilicon's CLN28HPC HBM Gen2 PHY Silicon Results



November 2015 TSMC
CyberShuttle with
interposer CoWoS



2D eye diagram for TT, 1.2V/0.9V and 25C
(~4mm interposer route)

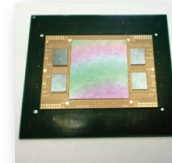


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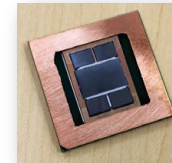
eSilicon HBM Customer Programs



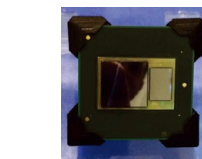
Organic Interposer
ASIC with four HBM1 stacks



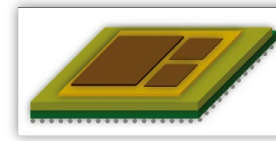
28nm
ASIC with four HBM1 stacks



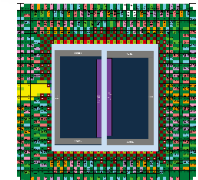
28nm
ASIC with four HBM2 stacks



FinFET
ASIC with one HBM2 stack



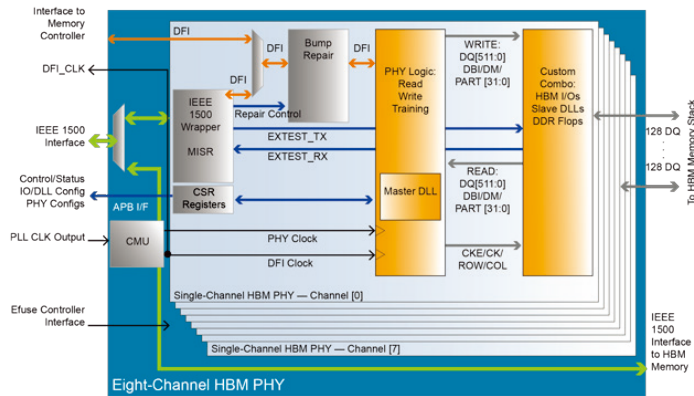
FinFET
ASIC with two HBM2 stacks



FinFET
Two ASIC dies
implementing chip-to-
chip communication

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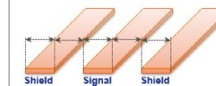
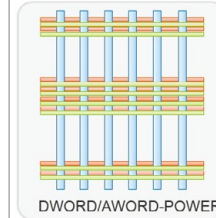
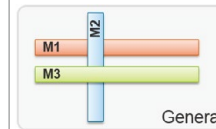
eSilicon HBM PHY IP



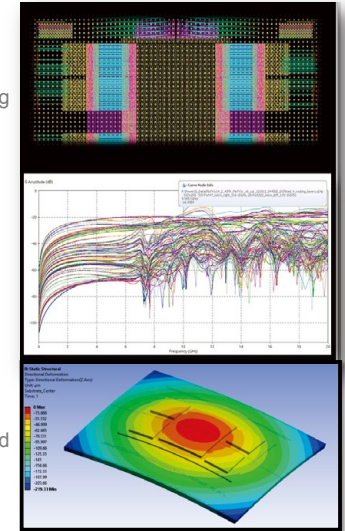
- All high-speed circuits are implemented with hand-crafted layout
- DFI and APB interfaces
- IEEE1500 and eFuse controller interfaces
 - PHY test modes, ubump repair, trimming

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eSilicon 2.5D Services



- **2.5D interposer and package design**
 - Interposer and package routing
 - Design for manufacturability (DFM)
 - SI/PI design and analysis
 - Thermal integrity
 - Warpage analysis
- **Single production source for:**
 - Acquisition / assignment of all die in package
 - Assembly
 - Test
 - Delivery of final, tested, yielded devices



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Interposer Technology Adoption



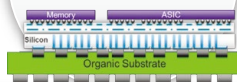
CoWoS

Trend #1

Extend the lifetime of existing packaging technologies

Trend #2

2.5D adoption for high-end markets at high price



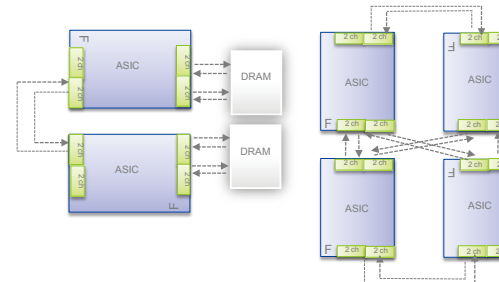
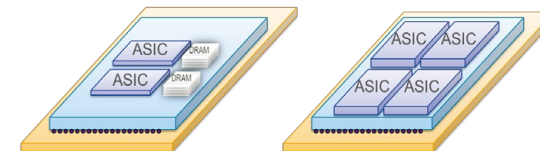
Trend #3

2.5D: Lower cost with build-up or organic interposers and use of FOWLP for additional connection density



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New Programs Combining HBM and Chip-to-Chip



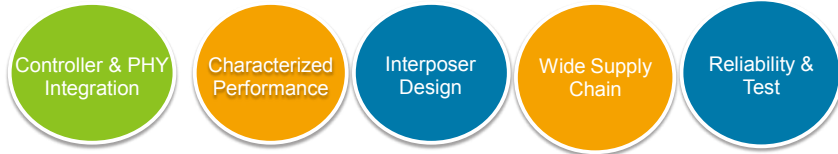
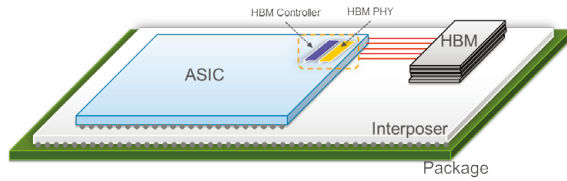
Combo PHY to support both HBM and chip-to-chip communication

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What's Needed for the Optimal HBM Implementation?



Achieving high-bandwidth and low-power benefits with a low-cost, low-risk, complete solution



eSilicon and TSMC have the solution



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